AUTOMOTIVE



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Vishay Siliconix

# Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0084
I <sub>D</sub> (A)	66
Configuration	Single
Package	PowerPAK SO-8L

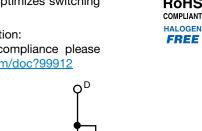
#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Q<sub>gd</sub>/Q<sub>gs</sub> ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

N-Channel MOSFET

-55 to +175

260



<b>ABSOLUTE MAXIMUM RATING</b>	<b>iS</b> ( $T_C = 25  ^{\circ}C$ , unless	otherwise noted)			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	40	V	
Gate-source voltage		$V_{GS}$	± 20	V	
Continuous drain current	T <sub>C</sub> = 25 °C	1	66		
	T <sub>C</sub> = 125 °C	l <sub>D</sub>	38		
Continuous source current (diode conduction)		I <sub>S</sub>	58	А	
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	168		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	22		
Single pulse avalanche energy	L = U.1 MH	E <sub>AS</sub>	24.2	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	р	65	W	
	T <sub>C</sub> = 125 °C	$P_{D}$	22		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	$R_{thJA}$	68	°C/W
Junction-to-case (drain)		$R_{thJC}$	2.3	C/VV

T<sub>J</sub>, T<sub>stg</sub>

#### Notes

a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %

Operating junction and storage temperature range

Soldering recommendations (peak temperature) c

- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

°С



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							•
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA		40	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A	-	0.0068	0.0084	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}$	I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.0128	Ω
		$V_{GS} = 10 \text{ V}$	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.0152	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	40	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	910	1274	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	362	508	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	43	60	
Total gate charge <sup>c</sup>	$Q_g$			-	15	20	
Gate-source charge c	$Q_{gs}$	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_{D} = 15 \text{ A}$	-	4.9	-	nC
Gate-drain charge <sup>c</sup>	$Q_{gd}$			-	3.5	-	
Gate resistance	$R_g$		f = 1 MHz	1.9	4.2	6.7	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	18	24	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 0.5 \Omega$ $I_{D} \cong 40 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	17	21	- ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	35	44	
Fall time <sup>c</sup>	t <sub>f</sub>			-	13	17	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	168	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	15 A, V <sub>GS</sub> = 0 V	-	-	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>			-	25	36	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	J <sub>-</sub> - 6	A, di/dt = 100 A/µs	-	10	14	nC
Reverse recovery fall time	t <sub>a</sub>	] IF = 0	n, αι/αι – 100 /ν μο	-	10	14	ns
Reverse recovery rise time	t <sub>b</sub>			-	15	21	110
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	0.8	1.1	Α

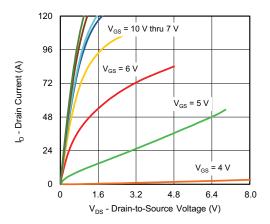
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

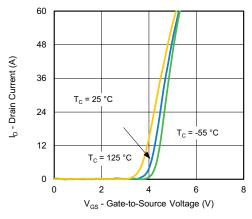
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



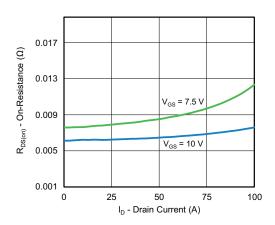
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



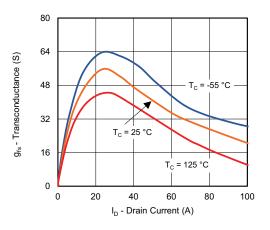
#### **Output Characteristics**



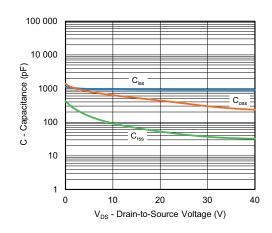
Transfer Characteristics



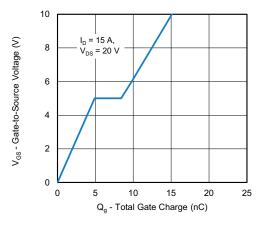
On-Resistance vs. Drain Current



Transconductance



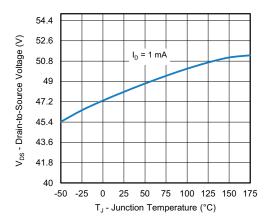
Capacitance



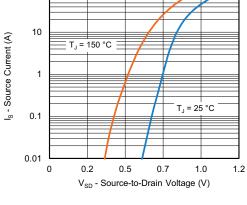
**Gate Charge** 



### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

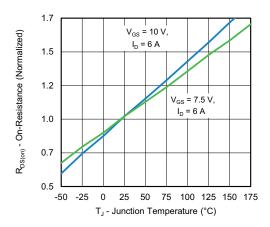


Drain Source Breakdown vs. Junction Temperature

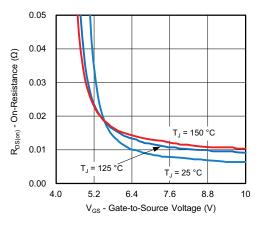


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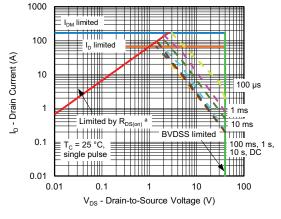
**Source Drain Diode Forward Voltage** 



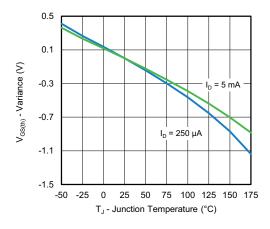
On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to Source Voltage



Safe Operating Area



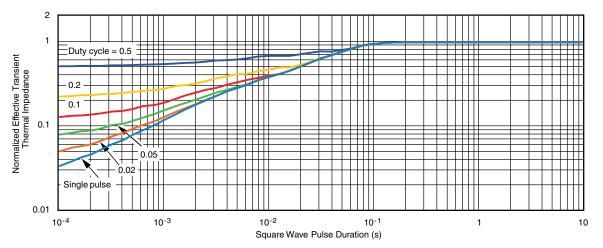
Variance vs. Junction Temperature

#### Note

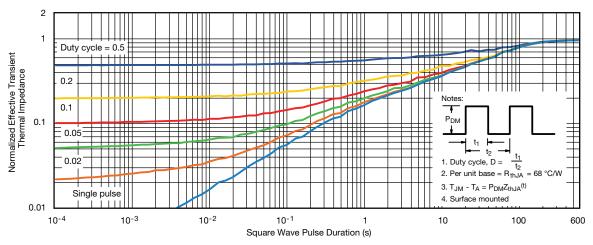
a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

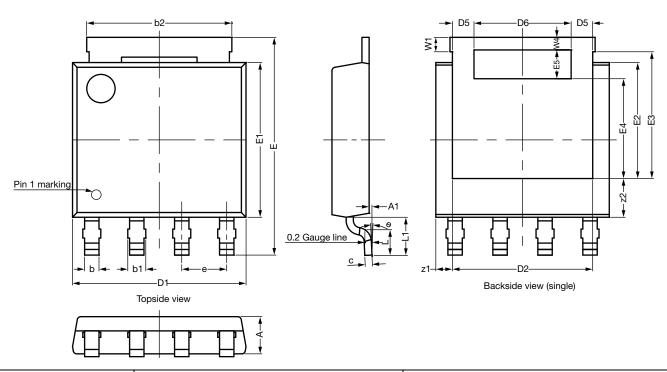
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?77299">www.vishay.com/ppg?77299</a>



# PowerPAK® SO-8L (PPKSO8LWLA) Case Outline 3



DIM.		MILLIMETERS		INCHES			
DIIVI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.00	1.05	1.10	0.039	0.041	0.043	
A1	0.00		0.127	0.000		0.005	
b	0.33	0.41	0.49	0.013	0.016	0.019	
b1	0.43	0.51	0.59	0.017	0.020	0.023	
b2	4.00	4.10	4.20	0.157	0.161	0.165	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D5	0.51	0.61	0.71	0.020	0.024	0.028	
D6	2.64	2.74	2.84	0.104	0.108	0.112	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
E3	3.48	3.58	3.68	0.137	0.141	0.145	
E4	2.72	2.82	2.92	0.107	0.111	0.115	
E5	0.71	0.81	0.91	0.028	0.032	0.036	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
W1	0.31	0.41	0.51	0.012	0.016	0.020	
W4	0.31	0.36	0.41	0.012	0.014	0.016	
z1	0.37	0.47	0.57	0.015	0.019	0.022	
z2	0.99	1.09	1.19	0.039	0.043	0.047	
θ	0°		5°	0°		5°	

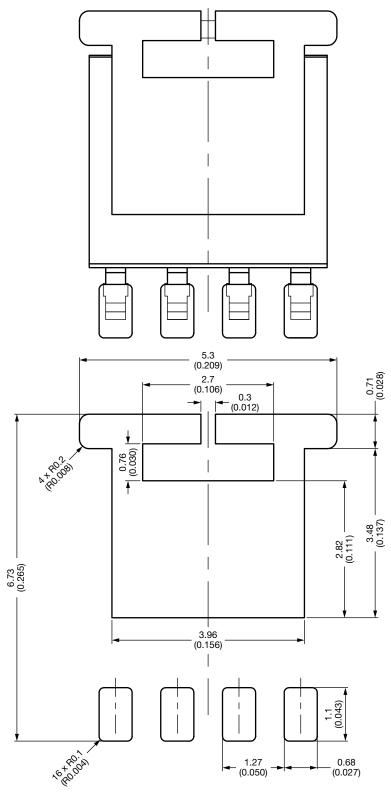
#### Note

• Millimeter will govern

Revison: 18-Sep-2023 1 Document Number: 76666



# Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)



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